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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, LINbus, MMC/SD, SAI, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	77
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	640K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 14x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l4r9vit6

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- Proprietary code readout protection (PCROP): a part of the Flash memory can be protected against read and write from third parties. The protected area is execute-only and it can only be reached by the STM32 CPU as an instruction code, while all other accesses (DMA, debug and CPU data read, write and erase) are strictly prohibited:
 - In single bank mode, two areas can be selected with 128-bit granularity.
 - In dual bank mode, one area per bank can be selected with 64-bit granularity.

An additional option bit (PCROP_RDP) allows to select if the PCROP area is erased or not when the RDP protection is changed from Level 1 to Level 0.

The whole non-volatile memory embeds the error correction code (ECC) feature supporting:

- Single error detection and correction
- Double error detection
- The address of the ECC fail can be read in the ECC register.

3.5 Embedded SRAM

The STM32L4R5xx, STM32L4R7xx and STM32L4R9xx devices feature 640 Kbytes of embedded SRAM. This SRAM is split into three blocks:

- 192 Kbytes mapped at address 0x2000 0000 (SRAM1).
- 64 Kbytes located at address 0x1000 0000 with hardware parity check (SRAM2). This memory is also mapped at address 0x2003 0000 offering a contiguous address space with the SRAM1. This block is accessed through the ICode/DCode buses for maximum performance. These 64 Kbytes SRAM can also be retained in Standby mode. The SRAM2 can be write-protected with 1 Kbyte granularity.
- 384 Kbytes mapped at address 0x2004 0000 - (SRAM3).

The memory can be accessed in read/write at CPU clock speed with 0 wait states.

3.10.6 VBAT operation

The VBAT pin allows to power the device VBAT domain from an external battery, an external supercapacitor, or from V_{DD} when there is no external battery and when an external supercapacitor is present. The VBAT pin supplies the RTC with LSE and the backup registers. Three anti-tamper detection pins are available in VBAT mode.

The VBAT operation is automatically activated when V_{DD} is not present. An internal VBAT battery charging circuit is embedded and can be activated when V_{DD} is present.

Note: When the microcontroller is supplied from VBAT, neither external interrupts nor RTC alarm/events exit the microcontroller from the VBAT operation.

3.11 Interconnect matrix

Several peripherals have direct connections between them, which allow autonomous communication between them and support the saving of CPU resources (thus power supply consumption). In addition, these hardware connections allow fast and predictable latency.

Depending on the peripherals, these interconnections can operate in Run, Sleep, Low-power run and Sleep, Stop 0, Stop 1 and Stop 2 modes. See [Table 6](#) for more details.

Table 6. STM32L4R5xx, STM32L4R7xx and STM32L4R9xx peripherals interconnect matrix

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low-power run	Low-power sleep	Stop 0 / Stop 1	Stop 2
TIMx	TIMx	Timers synchronization or chaining	Y	Y	Y	Y	-	-
	ADC DACx DFSDM1	Conversion triggers	Y	Y	Y	Y	-	-
	DMA	Memory to memory transfer trigger	Y	Y	Y	Y	-	-
	COMPx	Comparator output blanking	Y	Y	Y	Y	-	-
COMPx	TIM1, 8 TIM2, 3	Timer input channel, trigger, break from analog signals comparison	Y	Y	Y	Y	-	-
	LPTIMERx	Low-power timer triggered by analog signals comparison	Y	Y	Y	Y	Y	Y ⁽¹⁾
ADCx	TIM1, 8	Timer triggered by analog watchdog	Y	Y	Y	Y	-	-
RTC	TIM16	Timer input channel from RTC events	Y	Y	Y	Y	-	-
	LPTIMERx	Low-power timer triggered by RTC alarms or tamper	Y	Y	Y	Y	Y	Y ⁽¹⁾
All clocks sources (internal and external)	TIM2 TIM15, 16, 17	Clock source used as input channel for RC measurement and trimming	Y	Y	Y	Y	-	-

3.19 Analog-to-digital converter (ADC)

The device embeds a successive approximation analog-to-digital converters with the following features:

- 12-bit native resolution, with built-in calibration
- 5.33 Msps maximum conversion rate with full resolution
 - Down to 18.75 ns sampling time
 - Increased conversion rate for lower resolution (up to 8.88 Msps for 6-bit resolution)
- Up to 16 external channels
- 5 internal channels: internal reference voltage, temperature sensor, VBAT/3, DAC1 and DAC2 outputs
- One external reference pin is available on some package, allowing the input voltage range to be independent from the power supply
- Single-ended and differential mode inputs
- Low-power design
 - Capable of low-current operation at low conversion rate (consumption decreases linearly with speed)
 - Dual clock domain architecture: ADC speed independent from CPU frequency
- Highly versatile digital interface
 - Single-shot or continuous/discontinuous sequencer-based scan mode: 2 groups of analog signals conversions can be programmed to differentiate background and high-priority real-time conversions
 - Each ADC support multiple trigger inputs for synchronization with on-chip timers and external signals
 - Results stored into a data register or in RAM with DMA controller support
 - Data pre-processing: left/right alignment and per channel offset compensation
 - Built-in oversampling unit for enhanced SNR
 - Channel-wise programmable sampling time
 - Analog watchdog for automatic voltage monitoring, generating interrupts and trigger for selected timers
 - Hardware assistant to prepare the context of the injected channels to allow fast context switching

3.19.1 Temperature sensor

The temperature sensor (TS) generates a voltage V_{TS} that varies linearly with temperature. The temperature sensor is internally connected to the ADC1_IN17 input channels which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

Table 10. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
Advanced control	TIM1, TIM8	16-bit	Up, down, Up/down	Any integer between 1 and 65536	Yes	4	3
General-purpose	TIM2, TIM5	32-bit	Up, down, Up/down	Any integer between 1 and 65536	Yes	4	No
General-purpose	TIM3, TIM4	16-bit	Up, down, Up/down	Any integer between 1 and 65536	Yes	4	No
General-purpose	TIM15	16-bit	Up	Any integer between 1 and 65536	Yes	2	1
General-purpose	TIM16, TIM17	16-bit	Up	Any integer between 1 and 65536	Yes	1	1
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

3.30.1 Advanced-control timer (TIM1, TIM8)

The advanced-control timers can each be seen as a three-phase PWM multiplexed on six channels. They have complementary PWM outputs with programmable inserted dead-times. They can also be seen as complete general-purpose timers.

The four independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge or center-aligned modes) with full modulation capability (0-100%)
- One-pulse mode output

In debug mode, the advanced-control timer counter can be frozen and the PWM outputs disabled in order to turn off any power switches driven by these outputs.

Many features are shared with the general-purpose TIMx timers (described in [Section 3.30.2](#)) using the same architecture, so the advanced-control timers can work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

Figure 15. STM32L4R9xx UFBGA144 ballout⁽¹⁾

	1	2	3	4	5	6	7	8	9	10	11	12
A	VSS	PE0	PB9	PH3-BOOT0	PB4	VDDIO2	VSS	PD3	PC11	PA14	VDD	VSS
B	VBAT	VDD	PE3	PB8	PB5	PB3	PD6	PD1	PA15	PA13	PA12	PA11
C	VSS	PE5	PE2	PE1	PB7	PG13	PD4	PD0	PC10	PA10	VDDUSB	PC9
D	PC14-OSC32_IN	PC15-OSC32_OUT	PE4	PE6	PB6	PG12	PD5	PD2	PC12	PA9	PA8	PC6
E	PF2	PF1	PF0	PC13	PF3	PG10	PD7	PG8	PC7	PC8	PG7	VDDIO2
F	PF8	PF6	PF4	PF5	PF7	PG9	PG3	PG5	PG6	PG4	VSS	PG2
G	VDD	VSS	PF10	PF9	PF12	PE7	PD15	PD14	PD12	PD13	PD11	VDD
H	PH0-OSC_IN	PH1-OSC_OUT	PC0	PC2	PB2	PF15	PE11	PD10	PD9	PD8	DSI_D1P	DSI_D1N
J	NRST	PC1	PC3	PA6	PB1	PF13	PE9	PE13	PB15	VSSDSI	DSI_CKP	DSI_CKN
K	VSSA/VREF-	VREF+	PA0	PA4	PC5	PF11	PE8	PE15	PB11	PB14	DSI_D0P	DSI_D0N
L	VDDA	PA1	PA2	PA5	PC4	VSS	PG0	PE10	PB10	PB12	VDD	VCAPDSI
M	VSS	VDD	PA3	PA7	PB0	VDD	PF14	PG1	PE12	PE14	PB13	VSS

MSv38491V4

1. The above figure shows the package top view.

Figure 16. STM32L4R9xx WLCSP144 ballout⁽¹⁾

	1	2	3	4	5	6	7	8	9	10	11	12
A	VSS	PA14	PA15	PD0	PD5	VDD	PG12	VDDIO2	PB7	PE0	PE1	VSS
B	VDD	VDDUSB	PA13	PC12	PD2	VSS	PG10	PB3	PH3-BOOT0	PB9	PE2	VDD
C	PA11	PA12	PC10	PC11	PD1	PD4	PG9	PB4	PB6	PB8	PE3	PE4
D	PC8	PC9	PA8	PA9	PA10	PD3	PD7	PG13	PE5	PE6	PC13	VSS
E	PG7	PG8	VDDIO2	PC6	PG6	PC7	PD6	PB5	PF0	VBAT	PC14-OSC32_IN	PC15-OSC32_OUT
F	PD15	PG2	PD14	PD12	PG3	PG4	PG5	PF1	PF5	PF4	PF3	PF2
G	VSS	VDD	PD13	PD11	PD10	PE9	PF14	PA5	PF7	PF6	VSS	VDD
H	PD9	PD8	PB14	PB13	PE14	PE8	PB1	PA2	PC2	PF10	NRST	PH0-OSC_IN
J	DSI_D1N	DSI_D1P	PB15	PB12	PE13	PF15	PB2	PA6	PA0	PC3	PC0	PH1-OSC_OUT
K	DSI_CKP	DSI_CKN	VSSDSI	PE15	PE10	PG0	PF11	PC5	PA4	PA1	VSSA/VREF-	PC1
L	DSI_D0P	DSI_D0N	VCAPDSI	PB10	PE11	PG1	VDD	PF12	PC4	PA3	VREF+	VDDA
M	VDD	VDD	VSS	PB11	PE12	PE7	PF13	VSS	PB0	PA7	VDD	VSS

MSv42219V2

1. The above figure shows the package top view



Table 15. STM32L4Rxxx pin definitions (continued)

Pin number														Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32L4R5xxx, STM32L4R7xxx							STM32L4R9xxx												
LQFP100	BGA132_SMPS	BGA132	LQFP144_SMPS	LQFP144	WLCSP144	UFBGA169_SMPS	UFBGA169	LQFP100	LQFP144	UFBGA144	WLCSP144_SMPS	WLCSP144	UFBGA169						
-	M4	M4	-	-	-	N4	N4	-	-	-	-	-	-	OPAMP2_VINM	I	TT	-	-	-
32	J5	J5	43	43	M10	L4	L4	30	40	M4	M10	M10	M4	PA7	I/O	FT_fla	-	TIM1_CH1N, TIM3_CH2, TIM8_CH1N, I2C3_SCL, SPI1_MOSI, OCTOSPIM_P1_IO2, TIM17_CH1, EVENTOUT	OPAMP2_VINM, ADC1_IN12
33	K5	K5	44	44	L9	H5	H5	31	41	L5	L9	L9	K4	PC4	I/O	FT_a	-	USART3_TX, OCTOSPIM_P1_IO7, EVENTOUT	COMP1_INM, ADC1_IN13
34	L5	L5	45	45	K8	J5	J5	-	-	K5	K8	K8	-	PC5	I/O	FT_a	-	SAI1_D3, USART3_RX, EVENTOUT	COMP1_INP, ADC1_IN14, WKUP5
35	M5	M5	46	46	M9	K5	K5	32	42	M5	M9	M9	N4	PB0	I/O	TT_la	-	TIM1_CH2N, TIM3_CH3, TIM8_CH2N, SPI1_NSS, USART3_CK, OCTOSPIM_P1_IO1, COMP1_OUT, SAI1_EXTCLK, EVENTOUT	OPAMP2_VOUT, ADC1_IN15



Table 15. STM32L4Rxxx pin definitions (continued)

Pin number														Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32L4R5xxx, STM32L4R7xxx								STM32L4R9xxx											
LQFP100	BGA132_SMPS	BGA132	LQFP144_SMPS	LQFP144	WLCSP144	UFBGA169_SMPS	UFBGA169	LQFP100	LQFP144	UFBGA144	WLCSP144_SMPS	WLCSP144	UFBGA169						
42	M9	M9	64	64	L5	N8	N8	39	60	H7	L5	L5	N8	PE11	I/O	FT	-	TIM1_CH2, DFSDM1_CKIN4, TSC_G5_IO2, OCTOSPIM_P1_NCS, LCD_G4, FMC_D8, EVENTOUT	-
43	L9	L9	65	65	M5	M8	M8	40	61	M9	M5	M5	M8	PE12	I/O	FT	-	TIM1_CH3N, SPI1_NSS, DFSDM1_DATIN5, TSC_G5_IO3, OCTOSPIM_1_IO0, LCD_G5, FMC_D9, EVENTOUT	-
44	M10	M10	66	66	J5	L8	L8	41	62	J8	J5	J5	L8	PE13	I/O	FT	-	TIM1_CH3, SPI1_SCK, DFSDM1_CKIN5, TSC_G5_IO4, OCTOSPIM_P1_IO1, LCD_G6, FMC_D10, EVENTOUT	-



Table 15. STM32L4Rxxx pin definitions (continued)

Pin number														Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32L4R5xxx, STM32L4R7xxx								STM32L4R9xxx											
LQFP100	BGA132_SMPS	BGA132	LQFP144_SMPS	LQFP144	WLCSP144	UFBGA169_SMPS	UFBGA169	LQFP100	LQFP144	UFBGA144	WLCSP144_SMPS	WLCSP144	UFBGA169						
-	-	-	-	-	-	A2	A2	-	-	-	-	-	A2	PH2	I/O	FT	-	OCTOSPIM_P1_IO4, EVENTOUT	-
-	-	-	-	-	-	B2	B2	-	-	-	-	-	B2	PI7	I/O	FT	-	TIM8_CH3,DCMI_D7, EVENTOUT	-
-	-	-	-	-	-	B1	B1	-	-	-	-	-	B1	PI9	I/O	FT	-	OCTOSPIM_P2_IO2, CAN1_RX, EVENTOUT	-
-	-	-	-	-	-	A1	A1	-	-	-	-	-	A1	PI10	I/O	FT	-	OCTOSPIM_P2_IO1, EVENTOUT	-

1. PC13, PC14 and PC15 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 in output mode is limited:
 - The speed should not exceed 2 MHz with a maximum load of 30 pF
 - These GPIOs must not be used as current sources (for example to drive a LED).
2. After a Backup domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the RTC registers which are not reset by the system reset. For details on how to manage these GPIOs, refer to the Backup domain and RTC register descriptions in the RM0432 reference manual.
3. NC (not-connected) balls must be left unconnected. However, non connected (NC) GPIOs are not bonded. They must be configured by software to output push-pull and forced to 0 in the output data register to avoid extra current consumption in low-power modes.
4. After reset, these pins are configured as JTAG/SW debug alternate functions, and the internal pull-up on PA15, PA13, PB4 pins and the internal pull-down on PA14 pin are activated.

Table 18. STM32L4R5xx, STM32L4R7xx and STM32L4R9xx memory map and peripheral register boundary addresses⁽¹⁾ (continued)

Bus	Boundary address	Size (bytes)	Peripheral
APB2	0x4001 1C00 - 0x4001 1FFF	1 KB	FIREWALL
	0x4001 0800 - 0x4001 1BFF	5 KB	Reserved
	0x4001 0400 - 0x4001 07FF	1 KB	EXTI
	0x4001 0200 - 0x4001 03FF	1 KB	COMP
	0x4001 0030 - 0x4001 01FF	1 KB	VREFBUF
	0x4001 0000 - 0x4001 002F	1 KB	SYSCFG
APB1	0x4000 9800 - 0x4000 FFFF	26 KB	Reserved
	0x4000 9400 - 0x4000 97FF	1 KB	LPTIM2
	0x4000 8C00 - 0x4000 93FF	3 KB	Reserved
	0x4000 8400 - 0x4000 87FF	1 KB	I2C4
	0x4000 8000 - 0x4000 83FF	1 KB	LPUART1
	0x4000 7C00 - 0x4000 7FFF	1 KB	LPTIM1
	0x4000 7800 - 0x4000 7BFF	1 KB	OPAMP
	0x4000 7400 - 0x4000 77FF	1 KB	DAC1
	0x4000 7000 - 0x4000 73FF	1 KB	PWR
	0x4000 6800 - 0x4000 6FFF	2 KB	Reserved
	0x4000 6400 - 0x4000 67FF	1 KB	CAN1
	0x4000 6000 - 0x4000 63FF	1 KB	CRS
	0x4000 5C00 - 0x4000 5FFF	1 KB	I2C3
	0x4000 5800 - 0x4000 5BFF	1 KB	I2C2
	0x4000 5400 - 0x4000 57FF	1 KB	I2C1
	0x4000 5000 - 0x4000 53FF	1 KB	UART5
	0x4000 4C00 - 0x4000 4FFF	1 KB	UART4
	0x4000 4800 - 0x4000 4BFF	1 KB	USART3
	0x4000 4400 - 0x4000 47FF	1 KB	USART2
	0x4000 4000 - 0x4000 43FF	1 KB	Reserved
	0x4000 3C00 - 0x4000 3FFF	1 KB	SPI3
	0x4000 3800 - 0x4000 3BFF	1 KB	SPI2
	0x4000 3400 - 0x4000 37FF	1 KB	Reserved
	0x4000 3000 - 0x4000 33FF	1 KB	IWDG
	0x4000 2C00 - 0x4000 2FFF	1 KB	WWDG
	0x4000 2800 - 0x4000 2BFF	1 KB	RTC
	0x4000 1800 - 0x4000 23FF	4 KB	Reserved

6.3.4 Embedded voltage reference

The parameters given in [Table 25](#) are derived from tests performed under the ambient temperature and supply voltage conditions summarized in [Table 22: General operating conditions](#).

Table 25. Embedded internal voltage reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	$-40\text{ }^{\circ}\text{C} < T_A < +130\text{ }^{\circ}\text{C}$	1.182	1.212	1.232	V
$t_{S_vrefint}^{(1)}$	ADC sampling time when reading the internal reference voltage	-	4 ⁽²⁾	-	-	μs
$t_{start_vrefint}$	Start time of reference voltage buffer when ADC is enable	-	-	8	12 ⁽²⁾	μs
$I_{DD}(V_{REFINTBUF})$	V_{REFINT} buffer consumption from V_{DD} when converted by ADC	-	-	12.5	20 ⁽²⁾	μA
ΔV_{REFINT}	Internal reference voltage spread over the temperature range	$V_{DD} = 3\text{ V}$	-	5	7.5 ⁽²⁾	mV
T_{Coff}	Average temperature coefficient	$-40\text{ }^{\circ}\text{C} < T_A < +130\text{ }^{\circ}\text{C}$	-	30	50 ⁽²⁾	ppm/ $^{\circ}\text{C}$
A_{Coff}	Long term stability	1000 hours, $T = 25\text{ }^{\circ}\text{C}$	-	300	1000 ⁽²⁾	ppm
V_{DDCoff}	Average voltage coefficient	$3.0\text{ V} < V_{DD} < 3.6\text{ V}$	-	250	1200 ⁽²⁾	ppm/V
V_{REFINT_DIV1}	1/4 reference voltage	-	24	25	26	% V_{REFINT}
V_{REFINT_DIV2}	1/2 reference voltage		49	50	51	
V_{REFINT_DIV3}	3/4 reference voltage		74	75	76	

1. The shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design.

Table 40. Typical current consumption in Run and Low-power run modes, with different codes running from SRAM1

Symbol	Parameter	Conditions		Code	TYP	Unit	TYP	Unit
		-	Voltage scaling		25°C		25°C	
IDD (Run)	Supply current in Run mode	fHCLK=fHSE up to 48 MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	Range2 fHCLK=26 MHz	Reduced code ⁽¹⁾	3.35	mA	129	µA/MHz
				Coremark	3.10		119	
				Dhrystone2.1	3.65		140	
				Fibonacci	3.20		123	
				While ⁽¹⁾	2.85		110	
			Range 1 Normal Mode fHCLK= 80 MHz	Reduced code ⁽¹⁾	11.0	mA	138	µA/MHz
				Coremark	10.5		131	
				Dhrystone2.1	12.5		156	
				Fibonacci	10.5		131	
				While ⁽¹⁾	9.40		118	
			Range 1 Boost Mode fHCLK= 120 MHz	Reduced code ⁽¹⁾	18.0	mA	150	µA/MHz
				Coremark	16.5		138	
				Dhrystone2.1	19.5		163	
				Fibonacci	17.5		146	
				While ⁽¹⁾	15.0		125	
IDD(LPRun)	Supply current in Low-power run	fHCLK = fMSI = 2MHz all peripherals disable		Reduced code ⁽¹⁾	435	µA	218	µA/MHz
				Coremark	395		198	
				Dhrystone2.1	470		235	
				Fibonacci	425		213	
				While ⁽¹⁾	455		228	

1. Reduced code used for characterization results provided in [Table 26](#), [Table 30](#), [Table 34](#).



Table 47. Current consumption in Stop 1 mode

Symbol	Parameter	Conditions		TYP					MAX ⁽¹⁾					Unit
		-	VDD	25°C	55°C	85°C	105°C	125°C	25°C	55°C	85°C	105°C	125°C	
IDD (Stop 1)	Supply current in Stop 1 mode, RTC disabled	-	1.8 V	120	430	1400	2750	5050	280	1100	3300	6500	13000	μA
			2.4 V	120	430	1400	2750	5100	280	1100	3300	6500	13000	
			3 V	125	430	1400	2750	5100	280	1100	3300	6500	13000	
			3.6 V	120	430	1400	2750	5150	280	1100	3300	6600	13000 ⁽²⁾	
IDD (Stop 1 with RTC)	Supply current in STOP 1 mode, RTC enabled	RTC clocked by LSI	1.8 V	120	430	1400	2700	5050	280	1100	3300	6500	13000	
			2.4 V	125	430	1400	2750	5100	280	1100	3300	6500	13000	
			3 V	125	430	1400	2750	5100	280	1100	3300	6600	13000	
			3.6 V	125	435	1400	2750	5150	280	1100	3300	6600	13000	
		RTC clocked by LSE bypassed at 32768 Hz	1.8 V	120	430	1400	2750	5050	300	1100	3500	6900	13000	
			2.4 V	120	435	1400	2750	5100	300	1100	3500	6900	13000	
			3 V	125	435	1400	2750	5100	320	1100	3500	6900	13000	
			3.6 V	125	435	1400	2750	5150	320	1100	3500	6900	13000	
		RTC clocked by LSE quartz ⁽³⁾ in low drive mode	1.8 V	120	420	1350	2700	-	300	1100	3400	6800	-	
			2.4 V	120	420	1350	2700	-	300	1100	3400	6800	-	
			3 V	120	420	1350	2700	-	300	1100	3400	6800	-	
			3.6 V	120	425	1350	2700	-	300	1100	3400	6800	-	
IDD (wakeup from Stop 1)	Supply current during wakeup from Stop 1 mode	Wakeup clock is MSI = 48 MHz, voltage Range 1 ⁽⁴⁾	3 V	2.10	-	-	-	-	-	-	-	-	-	mA
		Wakeup clock is MSI = 4 MHz, voltage Range 2 ⁽⁴⁾	3 V	0.70	-	-	-	-	-	-	-	-	-	
		Wakeup clock is HSI = 16 MHz, voltage Range 1 ⁽⁴⁾	3 V	1.50	-	-	-	-	-	-	-	-	-	

1. Guaranteed by characterization results, unless otherwise specified.

2. Guaranteed by test in production.

3. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.

4. Wakeup with code execution from Flash. Average value given for a typical wakeup time as specified in [Table 53: Low-power mode wakeup timings](#)

6.3.7 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.

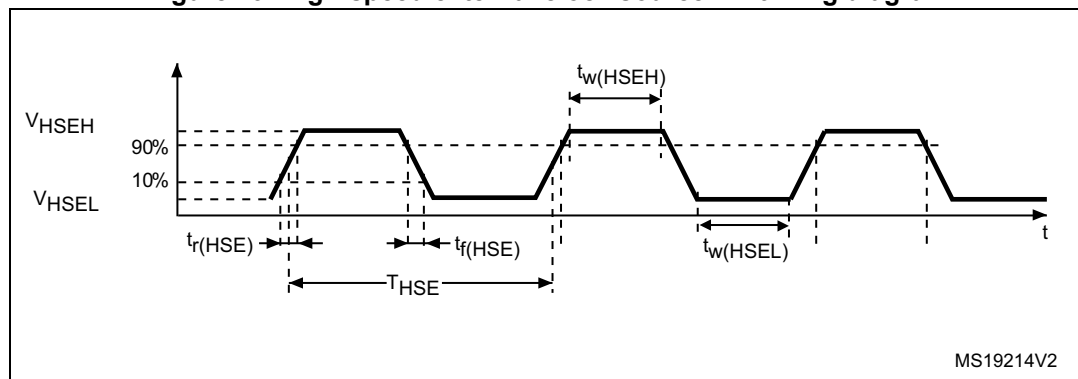
The external clock signal has to respect the I/O characteristics in [Section 6.3.17](#). However, the recommended clock input waveform is shown in [Figure 29: High-speed external clock source AC timing diagram](#).

Table 56. High-speed external user clock characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{\text{HSE_ext}}$	User external clock source frequency	Voltage scaling Range 1	-	8	48	MHz
		Voltage scaling Range 2	-	8	26	
V_{HSEH}	OSC_IN input pin high level voltage	-	$0.7 V_{\text{DDIOx}}$	-	V_{DDIOx}	V
V_{HSEL}	OSC_IN input pin low level voltage	-	V_{SS}	-	$0.3 V_{\text{DDIOx}}$	
$t_{\text{w(HSEH)}}$ $t_{\text{w(HSEL)}}$	OSC_IN high or low time	Voltage scaling Range 1	7	-	-	ns
		Voltage scaling Range 2	18	-	-	

1. Guaranteed by design.

Figure 29. High-speed external clock source AC timing diagram



6.3.9 PLL characteristics

The parameters given in [Table 64](#) are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in [Table 22: General operating conditions](#).

Table 64. PLL, PLLSAI1, PLLSAI2 characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PLL_IN}	PLL input clock ⁽²⁾	-	2.66	-	16	MHz
	PLL input clock duty cycle	-	45	-	55	%
$f_{PLL_P_OUT}$	PLL multiplier output clock P	Voltage scaling Range 1 Normal mode	2.0645	-	80	MHz
		Voltage scaling Range 1 Boost mode	2.0645	-	120	
		Voltage scaling Range 2	2.0645	-	26	
$f_{PLL_Q_OUT}$	PLL multiplier output clock Q	Voltage scaling Range 1 Normal mode	8	-	80	
		Voltage scaling Range 1 Boost mode	8	-	120	
		Voltage scaling Range 2	8	-	26	
$f_{PLL_R_OUT}$	PLL multiplier output clock R	Voltage scaling Range 1 Normal mode	8	-	80	
		Voltage scaling Range 1 Boost mode	8	-	120	
		Voltage scaling Range 2	8	-	26	
f_{VCO_OUT}	PLL VCO output	Voltage scaling Range 1	64	-	344	
		Voltage scaling Range 2	64	-	128	
t_{LOCK}	PLL lock time	-	-	15	40	μs
Jitter	RMS cycle-to-cycle jitter	System clock 80 MHz	-	40	-	±ps
	RMS period jitter		-	30	-	
$I_{DD(PLL)}$	PLL power consumption on V_{DD} ⁽¹⁾	VCO freq = 64 MHz	-	150	200	μA
		VCO freq = 96 MHz	-	200	260	
		VCO freq = 192 MHz	-	300	380	
		VCO freq = 344 MHz	-	520	650	

1. Guaranteed by design.

2. Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between the 3 PLLs.

6.3.10 MIPI D-PHY characteristics

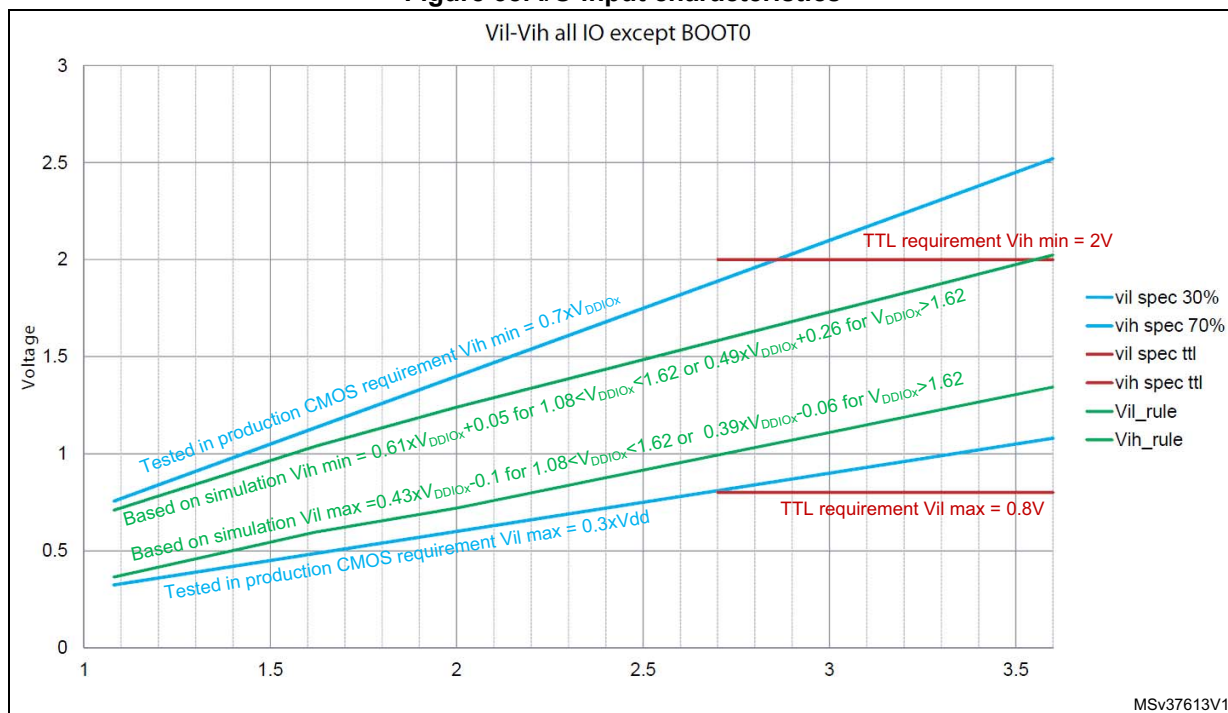
The parameters given in [Table 65](#) and [Table 66](#) are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in [Table 22](#).

1. Refer to [Figure 38: I/O input characteristics](#).
2. Tested in production.
3. Guaranteed by design.
4. $\text{Max}(V_{DDXX})$ is the maximum value of all the I/O supplies. Refer to [Table: Legend/Abbreviations used in the pinout table](#).
5. All TX_xx IO except FT_lu, FT_u, PB2 and PC3.
6. This value represents the pad leakage of the IO itself. The total product pad leakage is provided by this formula:

$$I_{\text{Total_leak_max}} = 10 \mu\text{A} + [\text{number of IOs where } V_{\text{IN}} \text{ is applied on the pad}] \times I_{\text{ikg}}(\text{Max}).$$
7. To sustain a voltage higher than $\text{MIN}(V_{\text{DD}}, V_{\text{DDA}}, V_{\text{DDUSB}}, V_{\text{LCD}}) + 0.3 \text{ V}$, the internal Pull-up and Pull-Down resistors must be disabled.
8. Refer to I_{bias} in [Table 92: OPAMP characteristics](#) for the values of the OPAMP dedicated input leakage current.
9. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimal (~10% order).

All I/Os are CMOS- and TTL-compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in [Figure 38](#) for standard I/Os, and in [Figure 38](#) for 5 V tolerant I/Os.

Figure 38. I/O input characteristics

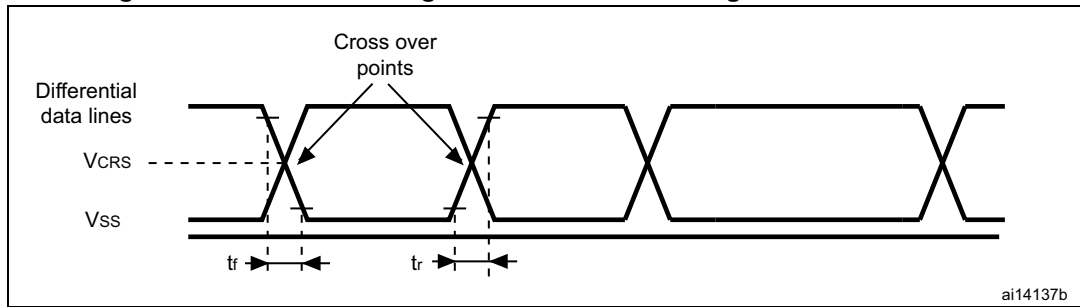


Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to $\pm 8 \text{ mA}$, and sink or source up to $\pm 20 \text{ mA}$ (with a relaxed V_{OL}/V_{OH}).

1. Guaranteed by design.
2. The I/O analog switch voltage booster is enable when $V_{DDA} < 2.4\text{ V}$ (BOOSTEN = 1 in the SYSCFG_CFGR1 when $V_{DDA} < 2.4\text{ V}$). It is disable when $V_{DDA} \geq 2.4\text{ V}$.
3. Fast channels are: PC0, PC1, PC2, PC3, PA0.
4. Slow channels are: all ADC inputs except the fast channels.

Figure 49. USB OTG timings – definition of data signal rise and fall time

Table 104. USB OTG electrical characteristics⁽¹⁾

Driver characteristics					
Symbol	Parameter	Conditions	Min	Max	Unit
t_{rLS}	Rise time in LS ⁽²⁾	$C_L = 200 \text{ to } 600 \text{ pF}$	75	300	ns
t_{fLS}	Fall time in LS ⁽²⁾				
t_{rfmLS}	Rise/ fall time matching in LS	t_r / t_f	80	125	%
t_{rFS}	Rise time in FS ⁽²⁾	$C_L = 50 \text{ pF}$	4	20	ns
t_{fFS}	Fall time in FS ⁽²⁾	$C_L = 50 \text{ pF}$			
t_{rfmFS}	Rise/ fall time matching in FS	t_r / t_f	90	111	%
V_{CRS}	Output signal crossover voltage (LS/FS)	-	1.3	2.0	V
Z_{DRV}	Output driver impedance ⁽³⁾	Driving high or low	28	44	Ω

1. Guaranteed by design
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).
3. No external termination series resistors are required on DP (D+) and DM (D-) pins since the matching impedance is included in the embedded driver.

Table 105. USB BCD DC electrical characteristics⁽¹⁾

Driver characteristics						
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{DD(USBBCD)}$	Primary detection mode consumption	-	-	-	300	μA
	Secondary detection mode consumption	-	-	-		
RDAT_LKG	Data line leakage resistance	-	300	-	-	k Ω
VDAT_LKG	Data line leakage voltage	-	0.0	-	3.6	V
RDCP_DAT	Dedicated charging port resistance across D+/D-	-	-	-	200	Ω
VLGC_HI	Logic high	-	2.0	-	3.6	V
VLGC_LOW	Logic low	-	-	-	0.8	V

Figure 65. OctoSPI Hyperbus read

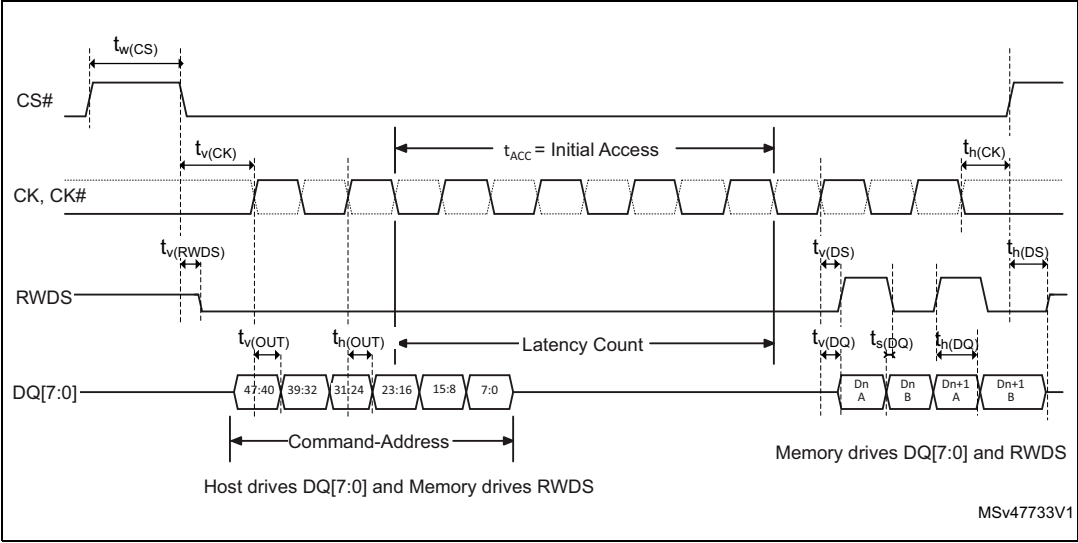
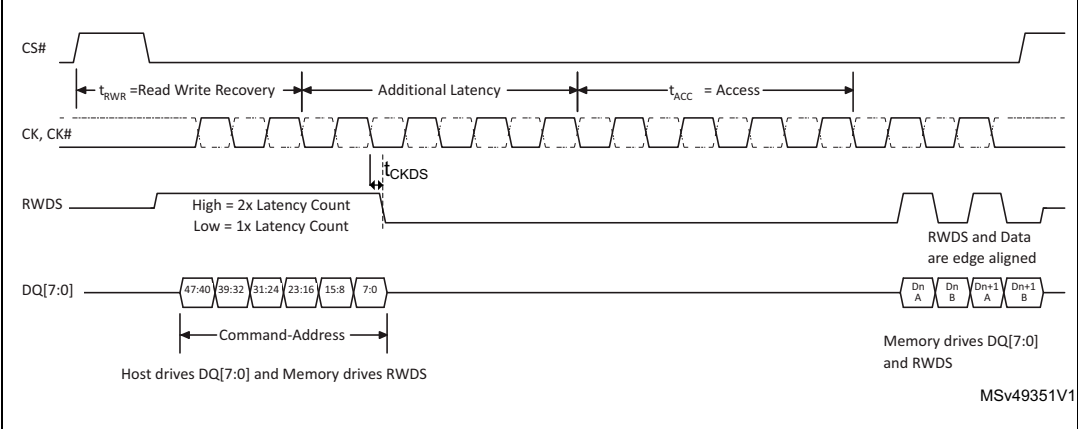


Figure 66. OctoSPI Hyperbus read with double latency

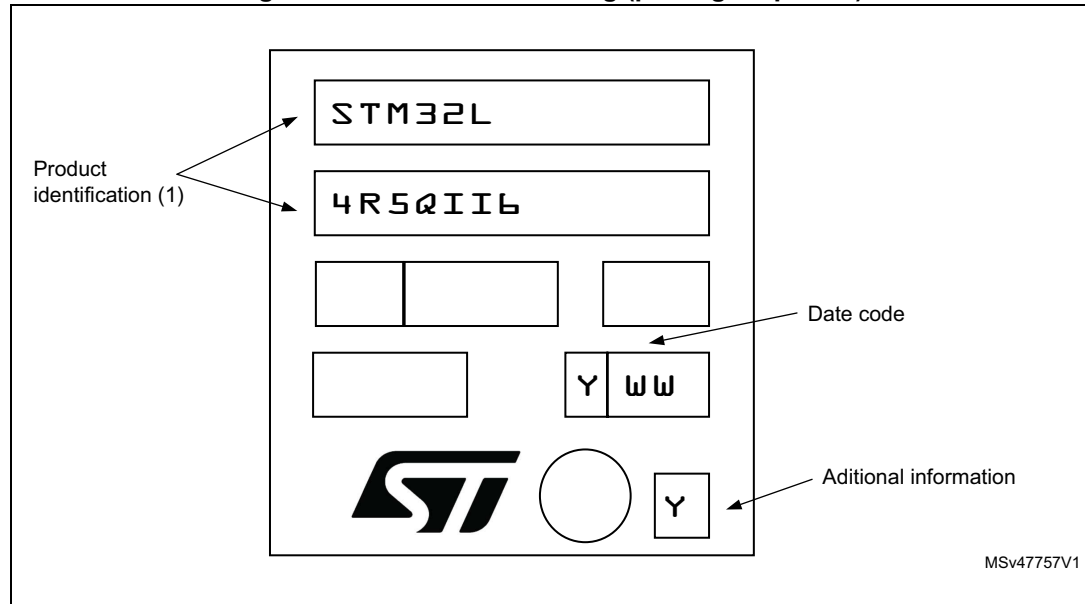


UFBGA132 device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 87. UFBGA132 marking (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.